

BLF6H10L-160; BLF6H10LS-160

Power LDMOS transistor

Rev. 2 — 12 December 2012

Product data sheet

1. Product profile

1.1 General description

A 160 W LDMOS RF power transistor for base station applications. The transistor can deliver 160 W from 729 MHz to 960 MHz. The excellent ruggedness and broadband performance of this device makes it ideal for base station applications.

Table 1. Typical performance

RF performance at $V_{DS} = 50$ V in a common-source Class-AB test circuit.

Test signal	f (MHz)	I_{DQ} (mA)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR (dBc)
2-carrier W-CDMA	960	600	50	38	20	34	-32 ^[1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01% probability on CCDF.

1.2 Features and benefits

- Integrated ESD protection
- Excellent ruggedness
- High power gain
- High efficiency
- Excellent reliability
- Easy power control
- Low R_{th} providing excellent thermal stability
- Low output capacitance for wideband performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- No internal matching for broadband applications
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power applications for GSM, GSM EDGE, W-CDMA, CDMA base stations and multi carrier applications in the 729 MHz to 960 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF6H10L-160 (SOT467C)			
1	drain		
2	gate		
3	source		
BLF6H10LS-160 (SOT467B)			
1	drain		
2	gate		
3	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF6H10L-160	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT467C
BLF6H10LS-160	-	earless ceramic package; 2 leads	SOT467B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_{L(AV)} = 70\text{ W}$	[1]	0.95 K/W

[1] $R_{th(j-c)}$ is measured under RF conditions.

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 4.5\text{ mA}$	[1]	104	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 450\text{ mA}$	[1]	1.4	1.7	2.4	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	1.4	μA	
I_{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	-	20.47	-	A	
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	140	nA	
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 135\text{ mA}$	[1]	-	1.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GSth} + 3.75\text{ V};$ $I_D = 15.75\text{ A}$	[1]	-	0.2	-	Ω

[1] I_D is the drain current.

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; PAR = 8.5 dB at 0.01 % probability on the CCDF; carrier spacing 5 MHz; 3GPP test model 1; 1-64 DPCH; $f_1 = 952.5\text{ MHz}; f_2 = 957.5\text{ MHz}$; RF performance at $V_{DS} = 50\text{ V}; I_{Dq} = 600\text{ mA}; T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 38\text{ W}$	18.8	20	-	dB
η_D	drain efficiency	$P_{L(AV)} = 38\text{ W}$	29	34	-	%
RL_{in}	input return loss	$P_{L(AV)} = 38\text{ W}$	-	-12	-6	dBc
ACPR	adjacent channel power ratio	$P_{L(AV)} = 38\text{ W}$	-	-32	-27	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF6H10L-160 and BLF6H10LS-160 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 50\text{ V}; f = 860\text{ MHz}$ at rated power.

7.2 Impedance information

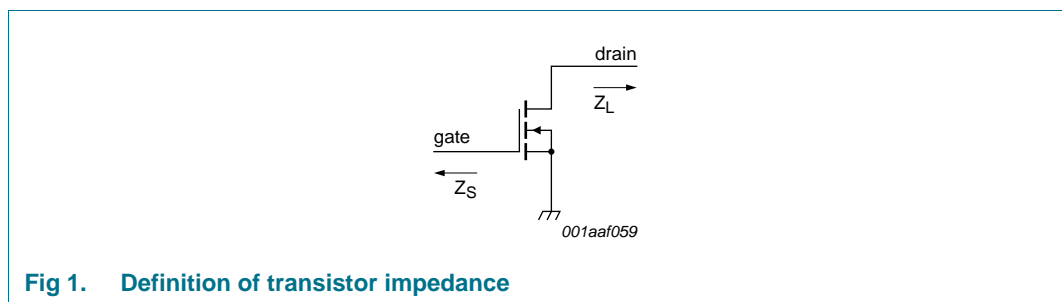
Table 8. Typical impedance

Simulated Z_S and Z_L test circuit impedances.

f (MHz)	Z_S (Ω)	Z_L (Ω)
729	1.0 – j0.8	3.1 + j1.7
760	1.0 – j0.7	3.0 + j1.5
790	1.0 – j0.7	2.8 + j1.4
820	1.0 – j0.6	2.7 + j1.2
869	1.0 – j0.5	2.5 + j1.0

Table 8. Typical impedance ...continued
 Simulated Z_S and Z_L test circuit impedances.

f (MHz)	Z_S (Ω)	Z_L (Ω)
881	$1.0 - j0.4$	$2.5 + j0.9$
894	$1.0 - j0.4$	$2.4 + j0.8$
920	$1.0 - j0.4$	$2.3 + j0.7$
940	$1.0 - j0.4$	$2.3 + j0.6$
960	$1.0 - j0.3$	$2.2 + j0.5$



7.3 Test circuit information

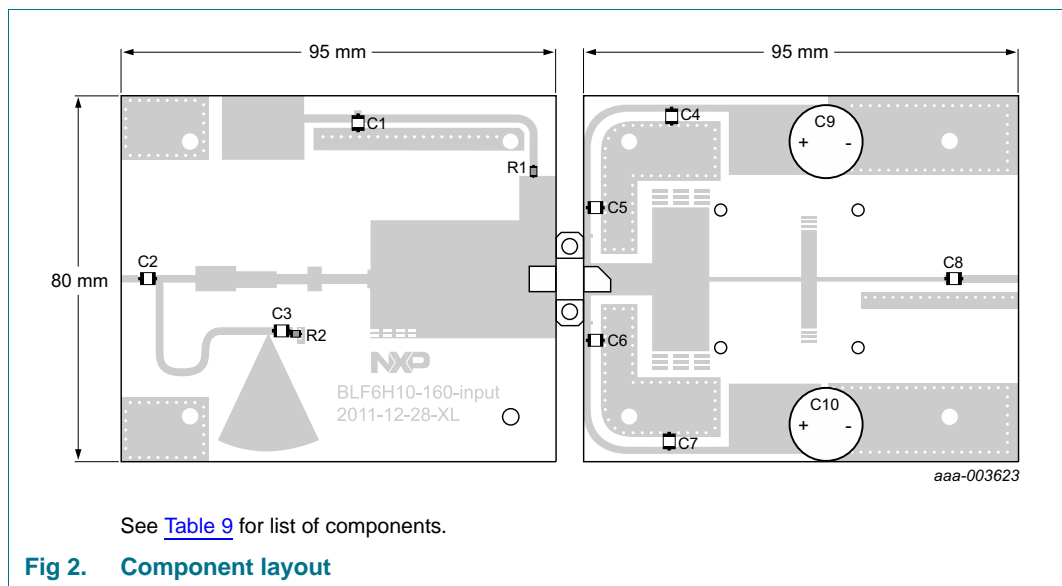
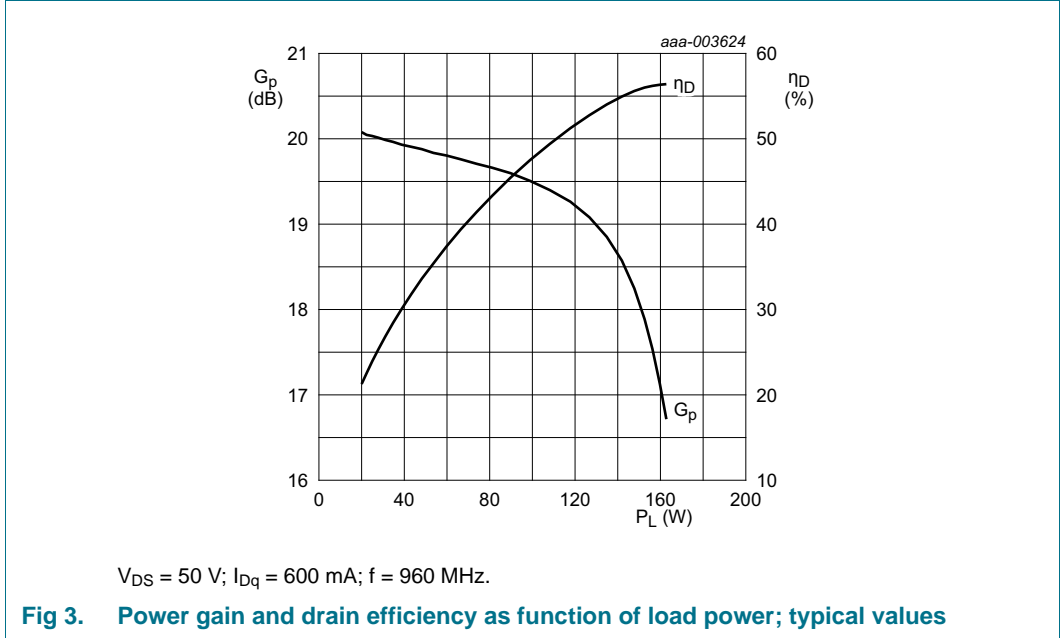


Table 9. List of components
 See [Figure 2](#) for component layout.

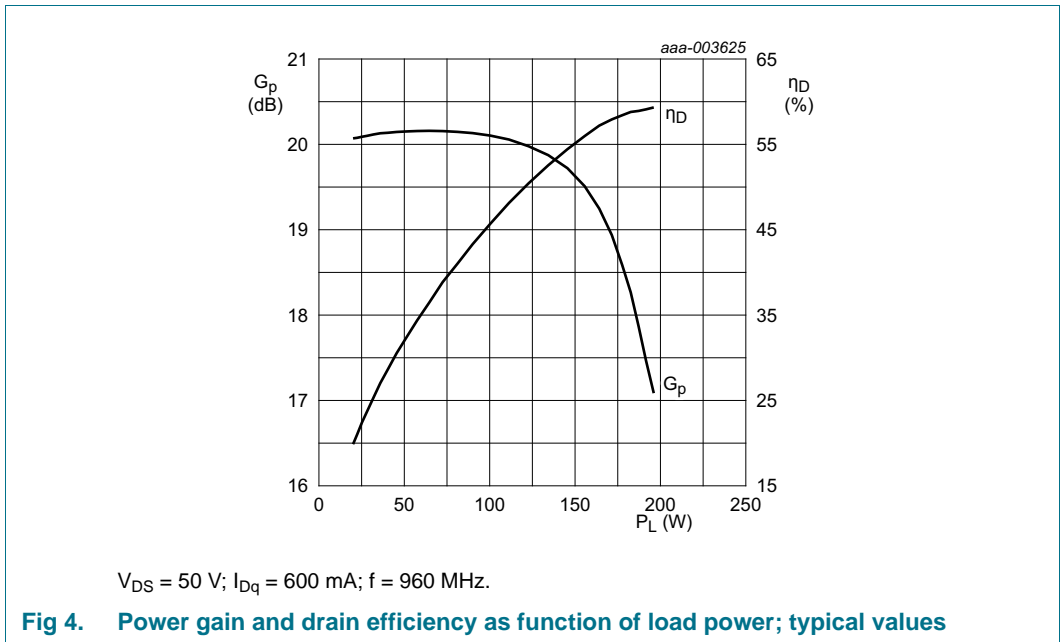
Component	Description	Value	Remarks
C1, C2, C3, C5, C6, C8	multilayer ceramic chip capacitor	47 pF	ATC100B
C4, C7	multilayer ceramic chip capacitor	1 μ F	Murata
C9, C10	electrolytic capacitor	1000 μ F, 100 V	
R1, R2	chip resistor	9.1 Ω	Vishale Dale 0805

7.4 Graphical data

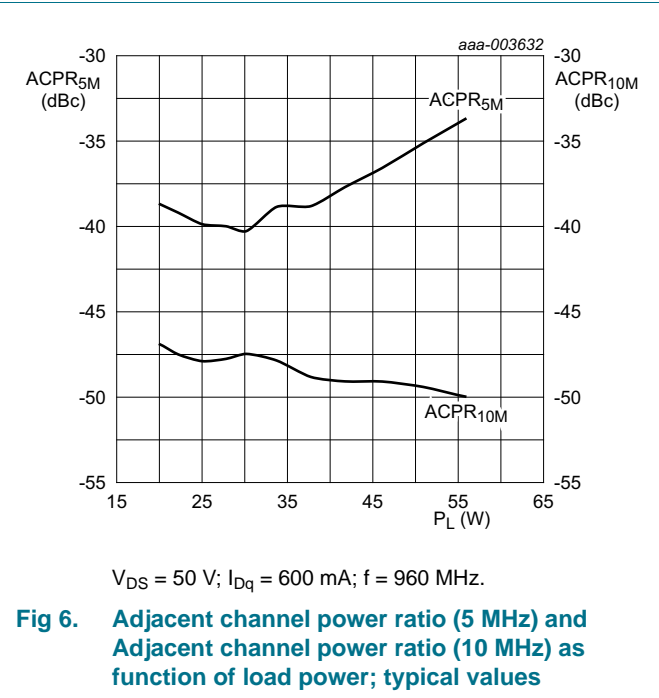
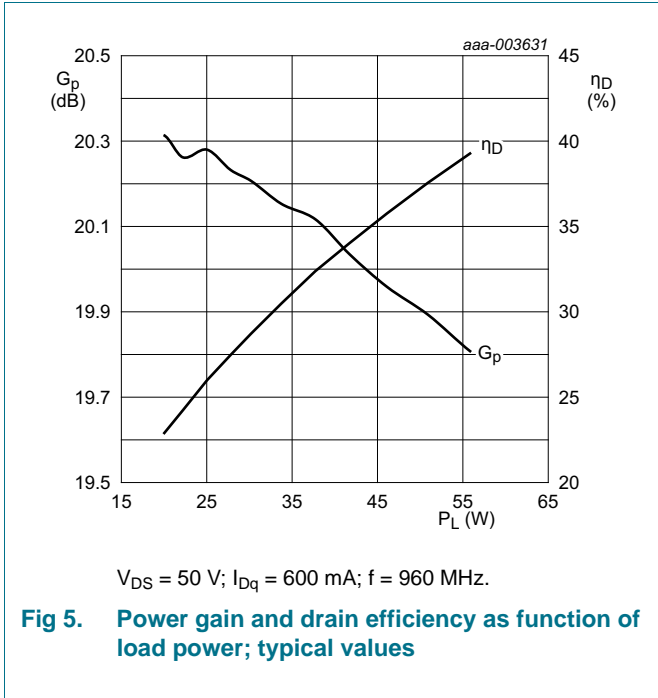
7.4.1 CW



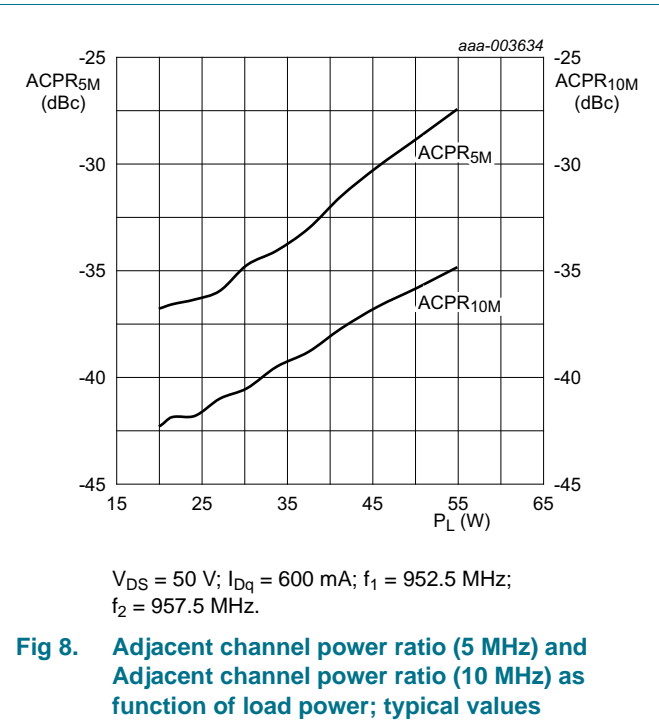
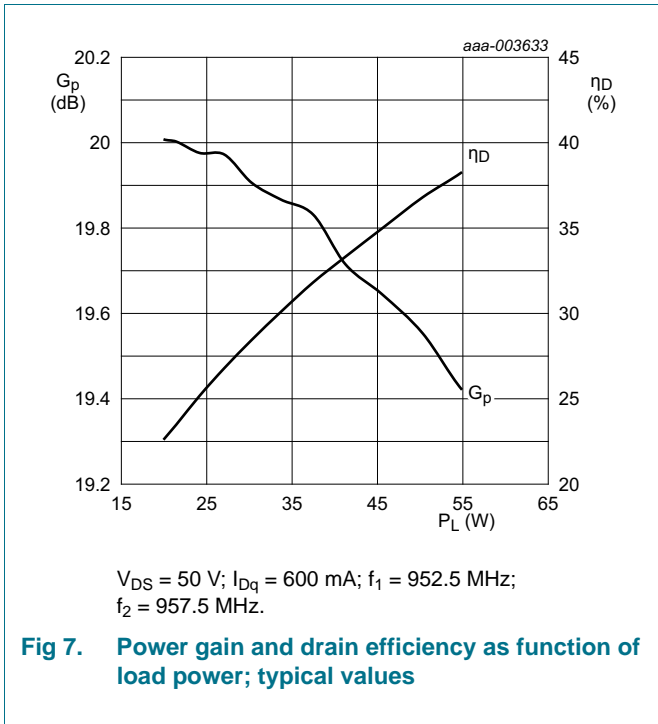
7.4.2 CW pulsed



7.4.3 1-Carrier W-CDMA



7.4.4 2-carrier W-CDMA



8. Package outline

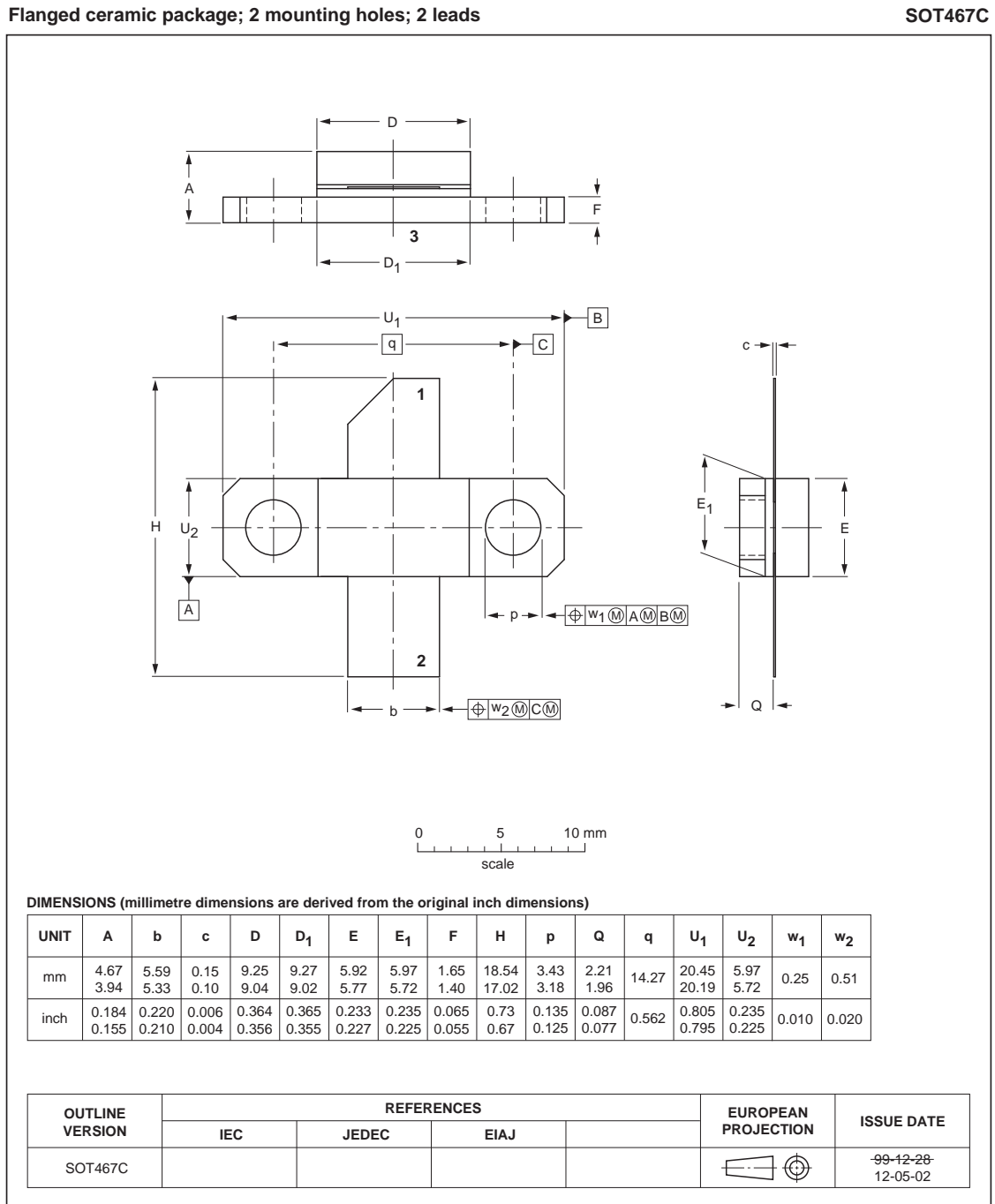


Fig 9. Package outline SOT467C

Earless ceramic package; 2 leads

SOT467B

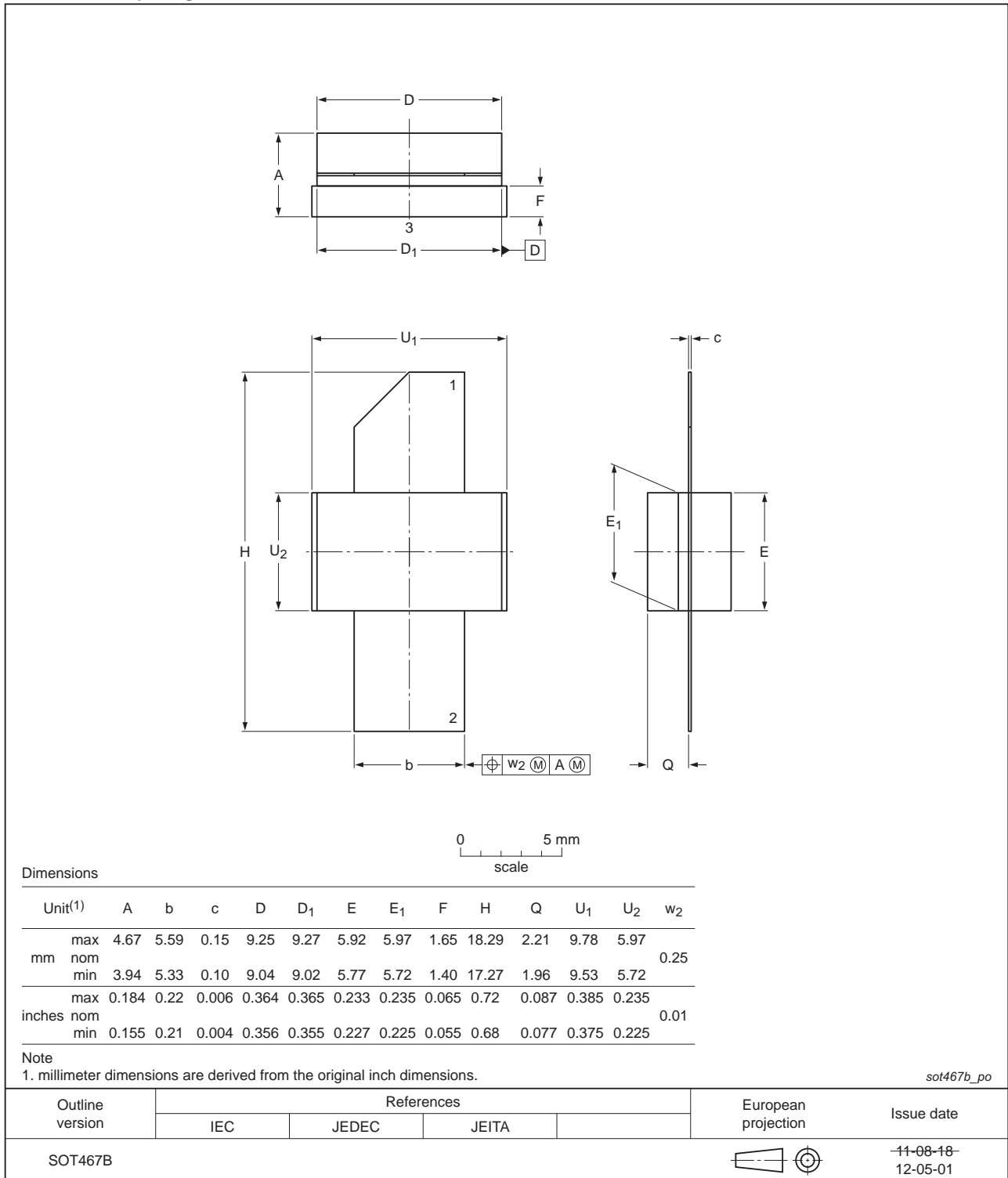


Fig 10. Package outline SOT467B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CDMA	Code Division Multiple Access
CCDF	Complementary Cumulative Distribution Function
DPCH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
GSM	Global System for Mobile Communications
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6H10L-160_6H10LS-160 v.2	20121212	Product data sheet	-	BLF6H10L-160_6H10LS-160 v.1
Modifications:				
<ul style="list-style-type: none"> • Section 1.1 on page 1: 'HF to 1 GHz' has been changed to '729 MHz to 960 MHz'. • Table 1 on page 1: table was updated. • Section 1.3 on page 1: '700 MHz to 1000 MHz' has been changed to '729 MHz to 960 MHz'. • Table 6 on page 3: table was updated. • Table 7 on page 3: table was updated. • Table 8 on page 3: table was updated. • Section 7.3 on page 4: added section. • Section 7.4 on page 5: added section. 				
BLF6H10L-160_6H10LS-160 v.1	20120210	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	2
6	Characteristics	3
7	Test information	3
7.1	Ruggedness in class-AB operation	3
7.2	Impedance information	3
7.3	Test circuit information	4
7.4	Graphical data	5
7.4.1	CW	5
7.4.2	CW pulsed	5
7.4.3	1-Carrier W-CDMA	6
7.4.4	2-carrier W-CDMA	6
8	Package outline	7
9	Handling information	9
10	Abbreviations	9
11	Revision history	9
12	Legal information	10
12.1	Data sheet status	10
12.2	Definitions	10
12.3	Disclaimers	10
12.4	Trademarks	11
13	Contact information	11
14	Contents	12

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